AMENDMENTS TO THE CLAIMS

1. (Currently amended) A liquid crystal display device provided with a plurality of gate lines on an insulating substrate, a plurality of data lines, and a plurality of TFTs, the gate lines crossing the data lines to define a pixel region and the TFTs being formed at crossing points of the gate and data lines, wherein a contact hole that electrically connects a drain electrode of the TFTs with a pixel electrode of the pixel region is formed over predetermined portions of the drain electrode and the pixel region to expose the insulating substrate through a gate insulating film and a passivation film and wherein the pixel electrode directly contacts the insulating substrate, the drain electrode, and a gate insulating film contacting a gate electrode.

2. (Currently amended) The liquid crystal display device as claimed in claim 1, wherein the TFTs and the pixel region comprises:

the gate electrode formed on the insulating substrate;

the gate insulating film formed on an entire surface of the insulating substrate including the gate electrode;

a semiconductor layer and an ohmic contact layer sequentially deposited at a predetermined portion on the gate insulating film;

source and drain electrodes formed right and left on the ohmic contact layer;

the [[a]] passivation film formed on the entire surface of the substrate including the source and drain electrodes;

the [[a]] contact hole formed by etching the passivation film to expose a predetermined portion of the drain electrode and a predetermined portion of the insulating substrate, where the [[a]] pixel electrode will be formed later; and

the pixel electrode formed on the passivation film and the contact hole.

3. (Currently amended) A liquid crystal display device comprising:

gate lines arranged to cross data lines on a substrate, thereby defining a pixel region;

thin film transistors, each having a gate electrode and source and drain electrodes, formed at crossing points of the gate lines and the data lines;

a contact hole formed over the drain electrode and the pixel region to expose the substrate through a gate insulating film and a passivation film; and

a pixel electrode formed in the pixel region for connecting the pixel electrode to the drain electrode through the contact hole, wherein the pixel electrode directly contacts the substrate, the drain electrode, and the [[a]] gate insulating film contacting the gate electrode.

4. (Original) The liquid crystal display device as claimed in claim 3, wherein the contact hole is formed over an edge part of the drain electrode and the pixel region adjacent to the edge part of the drain electrode.

5. (Currently amended) The liquid crystal display device as claimed in claim 3, wherein the each thin film transistor further comprises:

the [[a]] substrate on which the gate electrode is located;

the gate insulating film on an entire surface of the substrate including the gate electrode;

a semiconductor layer on the gate insulating film above the gate electrode;

the source and drain electrodes located at opposite sides of the semiconductor layer; and

the [[a]] passivation film formed on the entire surface of the substrate including the source and drain electrodes.

6. (Original) The liquid crystal display device as claimed in claim 5, wherein the contact hole is formed through passivation film on an edge part of the drain electrode and in the pixel region adjacent to the edge part of the drain electrode.

7. (Original) The liquid crystal display device as claimed in claim 5, wherein the contact hole is formed through the passivation film and the gate insulating film on an edge part of the drain electrode and in the pixel region adjacent to the edge part of the drain electrode.

8. (Currently amended) A method for fabricating the liquid crystal display device comprising:

forming thin film transistors each having a gate electrode, a source electrode and a drain on an insulating substrate;

forming a passivation film on an entire surface of the substrate including the thin film transistors;

forming a contact hole over a predetermined portion of the drain electrode and a pixel region adjacent to the drain electrode to expose the insulating substrate through the passivation film and a gate insulating film; and

forming a pixel electrode in the pixel region connected to the drain electrode through the contact hole, wherein the pixel electrode directly contacts the substrate, the drain electrode, and the [[a]] gate insulating film contacting the gate electrode.

9. (Original) The method as claimed in claim 8, wherein the contact hole is formed over an edge part of the drain electrode and the pixel region adjacent to the edge part of the drain electrode.

10. (Original) The method as claimed in claim 8, wherein the contact hole is formed by selectively removing the passivation film on an edge part of the drain electrode and the pixel region adjacent to the edge part of the drain electrode.

11. (Currently Amended) The method as claimed in claim 8, wherein forming the thin film transistors comprises:

forming the gate electrode on the insulating substrate;

forming the [[a]] gate insulating film on the entire surface of the insulating substrate including the gate electrode;

forming a semiconductor layer at a predetermined portion on the gate insulating film; and

respectively forming source and drain electrodes at opposite sides of the semiconductor layer.

12. (Original) The method as claimed in claim 11, wherein the contact hole is formed by selectively removing the passivation film and the gate insulating film on an edge part of the drain electrode and the pixel region adjacent to the edge part of the drain electrode.